Electrical and Optical Simulation of Organic Light-Emitting Diodes and White Organic Light-Emitting Diodes



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Contents

- Treating organic semiconductor with quantum drift-diffusion model.
- Light extraction using 3D ray-tracing (nonmicrocavity model).
- Electroluminescent spectra modeling with Frenkel exciton.
- Inclusion of microcavity effects.
- Application for AMOLED.
- Triplet diffusion and WOLED
- Low-voltage PIN structures
- Tandem OLED



Quantum drift-diffusion for OLED

- Quantum drift-diffusion model for current flow/spreading.
- Poole-Frenkel field dependent mobility model.
- Mobility-dependent bi-molecular radiative recombination model.
- Quantum tunneling model for Schottky barriers and heterojunctions.
- Self-heating model.
- Quantum wells?



An Example





Coordinates



Band Diagram



3D Potential Distribution



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3D Electron Density





3D Radiative Light Source





I-V Curve



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3D Ray-tracing with glass plate

external_package=plate

 n_0 - space_refr_index; n_1 - package_refr_index





3D Raytrace Power

Power (Watt/Stereo-radian)





Simulation statistics

TRANSMITTED POWER in absolute and relative to total (%) units THROUGH

-y side:

1.189041490400453E-008 26.159221035142593

+y side:

8.326234960594208E-010 1.831793276207384

-x side:

8.134143692337187E-009 17.895326992147012

+x side:

8.066635157261732E-009 17.746806464894195

-z side:

8.265096296359655E-009 18.183426115803123

+z side:

8.265096296359703E-009 18.183426115803226

→Glass substrate helps extract power



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Frenkel Exciton

- Organic semiconductor emits light via Frenkel exciton recombination.
- Conventional semiconductor theories based on free-carrier/many-body interband transition no longer valid.
- To establish optical spectrum model based on exciton-phonon interaction within an organic crystal.



<u>Hamiltonian</u>

- Hamiltonian established to include intramolecular and inter-molecular electronic and vibronic interactions.
- A phonon cloud of several unit cells is used to represent exciton-phonon interaction.
- All excited states of the molecular crystal are solved and optical transition dipole moments computed between all states.
- Model similar to Refs: [1] M. Hoffmann and Z. G. Soos, Phys. Rev. B 66, 024305 (2002)[2]Vragovic, R. Scholz and M. Schreiber, Europhysics Letters, vol. 57 (2), pp. 288-294, 2002.



Modeling Procedures

- Although mechanisms involved in the Hamiltonian are complex, input parameters are few and fitting to experimental spectrum is easy.
- Typical input/adjustable parameters: exciton bandgap, molecular vibronic quanta, intra-molecular exciton-phonon interaction constant, and inter-molecular hopping parameter.
- Doped organic semiconductor may easily be modeled as combination of emission from the host and the dopant separately.



Numerics

- Numerically efficient: several minutes per spectrum.
- Integrated into APSYS-OLED option so that optical extraction may be calculated based on the spectrum.
- Bias and current injection dependent spectrum may be simulated to fine tune the color of the OLED.



Typical EL/Absorption Spectra



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Some Fitted EL Spectra



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GHT



Applied electric field ranges from 1.E7 to 1.E8 V/m



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Theoretical Basis

- Self-consistent calculation of material spontaneous emission rate based on rigorous Frenkel exciton theories coupled with 2/3D simulation of current injection from the Crosslight APSYS drift-diffusion solver.
- Coupling of spontaneous emission with microcavity modes based on theory of C. H. Henry (1986) [1].
- Henry's theory has been extended from waveguide to RC-OLED by proper accounting of mode densities in a quasi-2D/3D emission situation.
- Photon recycling effects taken into account by accurate determination of photon power density inside the RCLED and self-consistent model of material absorption of the active layers in OLED.

[1] C. H. Henry, "Theory of spontaneous emission noise

in open resonators and its application to lasers and optical amplifiers,"

J. Lightwave Technol., vol. LT-4, pp. 288--297, March 1986.



An Example of RC-OLED

EL Emission



Structure according to C. Qiu, et. al. IEEE Trans. on Elec. Device, vol. 51,2004 p. 1207.

Strong microcavity effects reported for Type A.



Simulated band diagram





Leakage currents



Performance





→ Color changes with angle due to microcavity effect



Power vs. angle



→ Reasonable agreement with Type A experimental data



Spectrum



→ Narrower spectrum means resonance



Can be better?



→ Device may be optimized if position of emission source is adjusted to the peak of power.

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AMOLED Structure



(a) A more recent top-emitting OLED; (b) conventional bottomemitting OLED.

> Structure taken from Yang et. al, APL 87, 143507 (2005). We shall simulate top-emitting OLED here.





Band alignment


Radiative emitting source



Remark: simulation shows that only under some band alignment conditions will the emitting source be located at Alq3/alpha-NPD interface.



Simulated I-V versus experiment



Remark: by adjusting carrier lifetime, mobility, band alignment and metal work functions, reasonable agreement can be achieved over a few decades of current magnitude at higher voltage bias.



Simulated microcavity spectrum





→ Reasonable agreement with peak position and line width.



Simulated luminance



Agreement on luminance calculation is reasonable considering no fitting effort is made after I-V curve is calibrated. → We have a good IQE/extraction model for RC-OLED.



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Making use of triplets



Singlets may recombine to emit light
 Triplets are normally wasted unless harvested by phosphorescent dopants





Y. Sun, et. al. "Management of singlet and triplet excitons for efficient white organic light-emitting devices," Nature, Vol 440,13 April 2006, p. 908



Basic exciton diffusion equations for both singlet: and triplets [1]:

$$\begin{split} \frac{\partial S(x)}{\partial t} &= \gamma \cdot r(x) \cdot n(x) \cdot p(x) + D_S \cdot \frac{\partial^2 S(x)}{\partial x^2} - \frac{S(x)}{\tau} \\ &- \text{quenching_terms} \end{split}$$

Exciton quenching may include bulk/interface quenching and triplet-triplet biexciton quenching [2]

[1]B. Ruhstaller, et.al., "Simulating Electronic and Optical Processes in Multilayer Organic Light-Emitting Devices," IEEE J. SEL. TOPICS IN QUANTUM ELECTRONICS, VOL. 9,2003,p. 723.

[2] M. A. BALDO, et.al., "Transient analysis of organic electrophosphorescence. II. Transient analysis of triplet-triplet annihilation,"p. 10 967 PRB vol. 62, 2000



Some model details

- Biexciton quenching rate takes the form k_TT*S_T*S_T where S_T is triplet exciton density.
- Dopant dependent exciton lifetimes for different layers are adjusted to tune the color of the EL spectrum.
- Linear field dependent EL energy transfer from one dopant to another. This is used to model energy transfer from green dopant to red dopant.



Band alignment and carrier profile



Carrier profiles are sensitive to band alignments



Simulated I-V and P-I



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Exciton profiles





Triplet behavior



Exciton dipole profile



Remark: exciton radiation happens mainly in doped layers.



IQE behavior

Y. Sun, et. al. , Nature, Vol 440,13 April 2006, p. 908

Similar physical trends are obtained for quantum efficiency. Better fit may be obtained if more quenching terms are included.





Stable white color obtained



Spectrum obtained at 4, 8, 12 and 16 volts of bias.



Normalized EL spectrum



Y. Sun, et. al., Nature, Vol 440,13 April 2006, p. 908

Based on previous experiments from the same authors, exciton lifetimes were set at 1-100 of micro-seconds and adjusted to match experimental spectrum.



Biexciton quenching





Triplet dopant-dopant energy tranfer



Summary on WOLED simulation

Based on simulation and analysis using APSYS, we find

- Triplet profile determined by band alignment.
- White color stability relies on multiple factors such as single/triplet ratio, field dependent exciton lifetime, triplet-triplet quenching and dopant to dopant energy transfer.
- Simulation may help gain insight into and help design better WOLED.



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Layer Structure & Model

- ITO/glass substrate
- p-doped HTL (100 nm) : m-MTDATA:F₄-TCNQ (2% mol.)
- TPD (5 nm): carrier confinement
- Alq3 (20 nm) : active region @ 530 nm
- Bphen (10 nm) : carrier confinement
- n+-doped ETL (30 nm) : Bphen:Li (1:1 ratio)
- LiF (1 nm)/AI contact
- Contacts defined as Schottky
- Energy levels of electrical dopants included to account for incomplete ionization
- Quantum tunneling defined for contact and TPD regions due to band alignment
- RCLED model used

Based on J. Huang & al., "Low-voltage organic electroluminescent devices using *pin* structures", Appl. Phys. Lett., Vol. 80 No.1, 7 Jan. 2002



Band diagram @ 2V bias



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Simulated I-V versus experiment



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Simulated L-V versus experiment



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Internal Quantum Efficiency



Note: Efficiency limited to 25% since there is no triplet harvesting.



Comments

- Very reasonable fit to experiment over 4 decades of current values and 6 decades of luminance
- Low turn-on voltage, close to thermodynamic limit of Alq3
- High efficiency limited by singlet-only design. Can be improved by triplet harvesting as in previous WOLED design
- Efficiency fit can be improved by adding quenching terms which are important at higher bias values
- PIN design lends itself well to solar cell applications



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Layer structure of tandem OLED

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evice or unit	Layer structure
Device A	ITO/SA1/ <u>EL-G</u> /OC1/ <u>EL-R</u> /SC1/Mg:Ag
Device B	ITO/SA1/EL-G/EL-R/SC1/Mg:Ag
Device C	ITO/SA1/EL-G/SC1/Mg:Ag
Device D	ITO/SA1/ <u>EL-R</u> /SC1/Mg:Ag
SA1	NPB (50 nm)
EL-G	NPB (25 nm)/Alq (20 nm)/Alq (5 nm)
OC1	Alq:Li (25 nm)/NPB:FeCl ₃ (60 nm)
EL-R	NPB (25 nm)/Alq:DCJTB (20 nm)/Alq (5 nm)
SC1	Alq (35 nm)

Based on Liao, Klubek, and Tang, "High-efficiency tandem organic lightemitting diodes," Appl. Phys. Lett., Vol. 84, No. 2, 12 January 2004, p.167

Model requirements: treatment of n-type and p-type dopings, tunnel junction, and microcavity effects due to multiple colors with dipole source distributed in multiple locations.



Tunnel Junction for OLED





- a) Band diagram at 4 volt;
- b) at 14.2 volt;
- c) Exciton distribution at 14.2 volt.



Simulated EL spectrum



Optical phase in microcavity model, band alignment and mobility were found to affect the color and intensity of the EL spectra. Reason results were obtained after careful choice of parameters.





Experimental findings: Device A with tunnel junction (TJ),
V=14.2 V at 20 mA/cm²; Device B, V=16 V at 20 mA/cm².
→ Electrical doping and TJ reduces operating voltage by about 2 volts.



More tandem structures

Device or unit	Layer structure
Device E	ITO/SA2/ <u>EL2</u> /SC2/Mg:Ag
Device F	ITO/SA2/EL2/OC2/EL2/SC2/Mg:Ag
Device G	ITO/SA2/EL2/OC2/EL2/OC2/EL2/SC2/Mg:Ag
Device H	ITO/SA2/EL2/EL2/EL2/SC2/Mg:Ag
SA2	NPB (60 nm)
EL2	NPB (30 nm)/Alq:C545T (20 nm)/Alq (10 nm)
OC2	Alq:Li (30 nm)/NPB:FeCl ₃ (60 nm)
SC2	Alq (30 nm)

Based on Liao, Klubek, and Tang, "High-efficiency tandem organic lightemitting diodes," Appl. Phys. Lett., Vol. 84, No. 2, 12 January 2004, p.167

Model requirements: treatment of n-type and p-type dopings, tunnel junction. Microcavity effects neglected for simplicity here.







Exciton at 20 mA/cm^2




Conclusions

- A rather comprehensive set of modules suitable for OLED and WOLED simulation implemented in APSYS for both electrical and optical modeling.
- Each module may be used independently or in a fully integrated manner.
- All critical modules have been verified by experiments.

